



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
60V	5.0Ω @ $V_{GS} = 10V$	230mA
6UV	7.5Ω @ V _{GS} = 5V	190mA

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

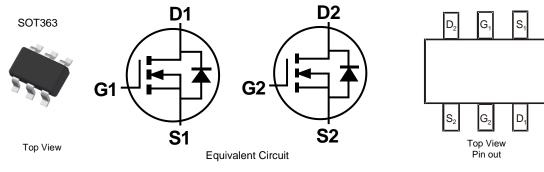
- Motor Control
- Power Management Functions

Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)



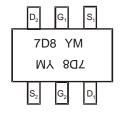
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN67D8LDW-7	SOT363	3000/Tape & Reel
DMN67D8LDW-13	SOT363	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



7D8 = Product Type Marking Code YM = Date Code Marking Y or Y = Year (ex: C = 2015) M = Month (ex: 9 = September)

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	В	С	D	Е	F	G	Н		J	K	L	М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	60	V	
Gate-Source Voltage		V_{GSS}	±30	V	
Continuous Drain Current (Note 6) $V_{GS} = 10V$ Steady $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$			I _D	230 180	mA
Maximum Continuous Body Diode Forward Curren	t (Note 6)	I _S	0.5	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	6) (Note 6)	I _{DM}	0.8	Α	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	320	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	400	°C/W
Total Power Dissipation (Note 6)		P_{D}	410	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	312	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

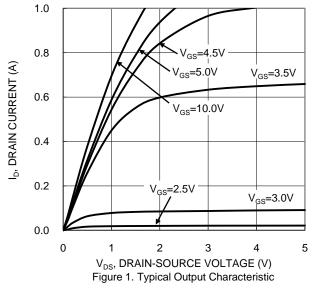
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

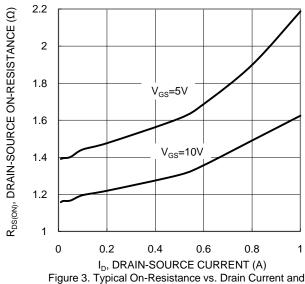
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_{D} = 10\mu A$
Zero Gate Voltage Drain Current	I _{DSS}		-	1.0	μΑ	$V_{DS} = 60V$, $V_{GS} = 0V$
Gate-Source Leakage	IGSS	-	_	±100	nΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	_	2.5	V	$V_{DS} = 10V, I_D = 250\mu A$
Static Drain-Source On-Resistance	D-s/s/s		1.5	5.0	Ω	$V_{GS} = 10V, I_D = 0.5A$
Static Dialif-Source Off-Resistance	R _{DS(ON)}		3.2	7.5	12	$V_{GS} = 5V, I_D = 0.05A$
Forward Transfer Admittance	Y _{fs}	80	_	_	mS	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage	V_{SD}		0.78	1.5	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	-	22	_	рF	V 0514 14 014
Output Capacitance	Coss	-	4.1	_	рF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	Crss	l	2.5		pF	1 - 1.01VII 12
Gate Resistance	R_g	1	120	_	Ω	$f = 1.0MHz$, $V_{GS} = 0V$, $V_{DS} = 0V$
Total Gate Charge (V _{GS} = 4.5V)	Q_{g}	l	361	_	рС	
Total Gate Charge (V _{GS} = 10V)	Qg	-	821	_	рС	$V_{GS} = 4.5V, V_{DS} = 10V,$
Gate-Source Charge	Q_{gs}	1	162	_	рС	$I_D = 250 \text{mA}$
Gate-Drain Charge	Q_{gd}	-	116	_	рС	
Turn-On Delay Time	t _{D(ON)}		2.8	_	ns	
Turn-On Rise Time	t _R		3.0	_	ns	$V_{DD} = 30V, I_D = 0.2A,$
Turn-Off Delay Time	t _{D(OFF)}		7.6	_	ns	$R_L = 150\Omega$, $V_{GS} = 10V$, $R_G = 25\Omega$
Turn-Off Fall Time	t _F	_	5.6	_	ns	

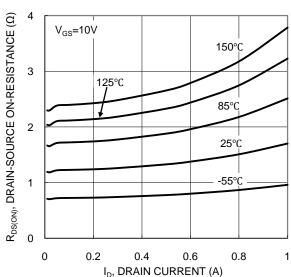
Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.



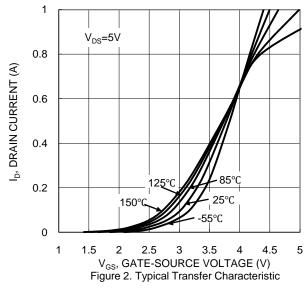


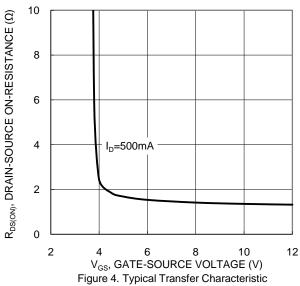




Gate Voltage

Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature





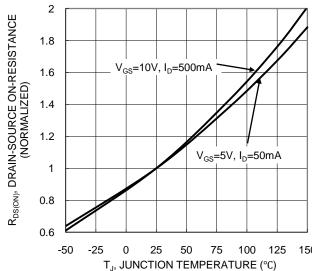


Figure 6. On-Resistance Variation with Junction Temperature



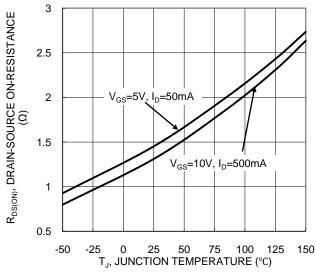
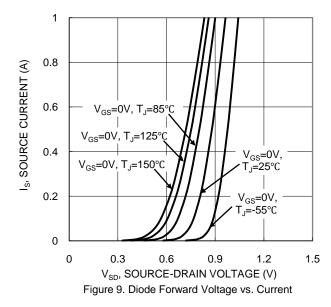
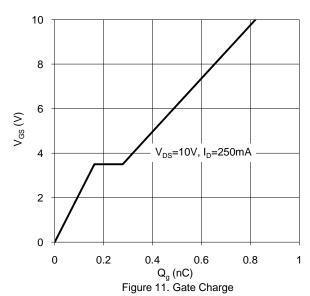


Figure 7. On-Resistance Variation with Junction Temperature





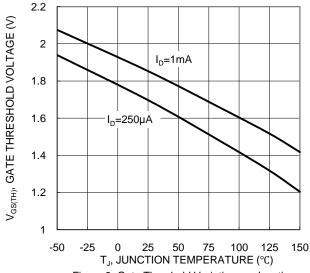
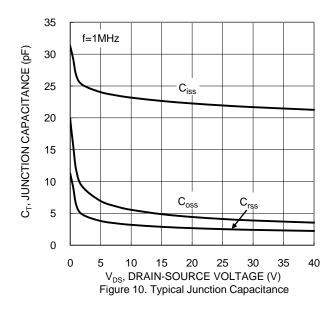


Figure 8. Gate Threshold Variation vs. Junction Temperature



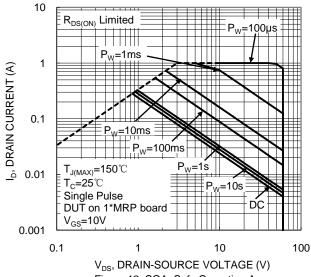
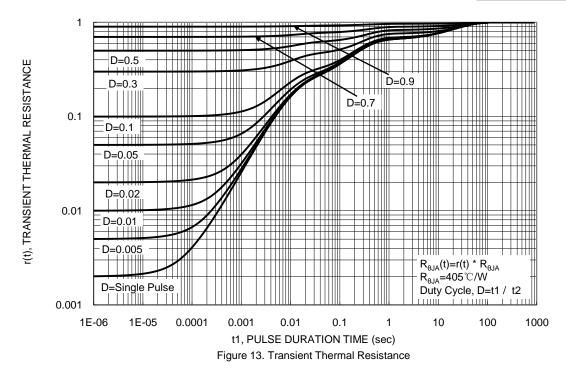


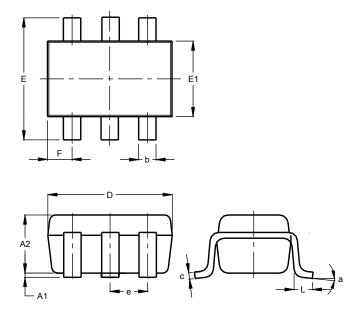
Figure 12. SOA, Safe Operation Area





Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

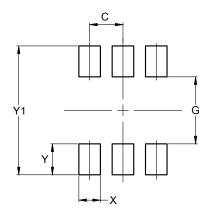


SOT363								
Dim	Min	Max	Тур					
A1	0.00	0.10	0.05					
A2	0.90	1.00	1.00					
b	0.10	0.30	0.25					
С	0.10	0.22	0.11					
D	1.80	2.20	2.15					
E	2.00	2.20	2.10					
E1	1.15	1.35	1.30					
е	0.650 BSC							
F	0.40	0.45	0.425					
L	0.25	0.40	0.30					
а	a 8°							
All	All Dimensions in mm							



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.420
Y	0.600
Y1	2.500

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